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Team Nexperia

PEMH15; **PUMH15**

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

Rev. 5 — 16 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN/NPN double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,				PNP/PNP	Package	
	NXP	JEITA	complement	complement	configuration		
PEMH15	SOT666	-	PEMD15	PEMB15	ultra small and flat lead		
PUMH15	SOT363	SC-88	PUMD15	PUMB15	very small		

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		8.0	1	1.2	



2. Pinning information

Table 3. Pinning

Table 3.	riiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1 R1 1 2 3
			sym063

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMH15	-	plastic surface-mounted package; 6 leads	SOT666
PUMH15	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMH15	5F
PUMH15	H2*

[1] * = placeholder for manufacturing site code

5. Limiting values

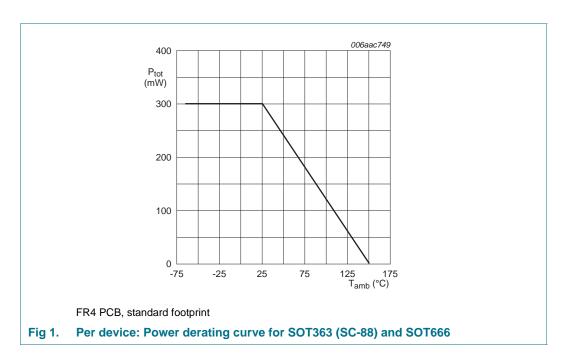
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

_				
Parameter	Conditions	Min	Max	Unit
stor				
collector-base voltage	open emitter	-	50	V
collector-emitter voltage	open base	-	50	V
emitter-base voltage	open collector	-	10	V
input voltage				
positive		-	+30	V
negative		-	-10	V
output current		-	100	mA
peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
PEMH15 (SOT666)		[1][2] _	200	mW
PUMH15 (SOT363)		<u>[1]</u> -	200	mW
,				
total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
PEMH15 (SOT666)		[1][2] _	300	mW
PUMH15 (SOT363)		[1] -	300	mW
junction temperature		-	150	°C
ambient temperature		-65	+150	°C
storage temperature		-65	+150	°C
	collector-base voltage collector-emitter voltage emitter-base voltage input voltage positive negative output current peak collector current total power dissipation PEMH15 (SOT363) total power dissipation PEMH15 (SOT363) junction temperature ambient temperature	collector-base voltage open emitter collector-emitter voltage open base emitter-base voltage open collector input voltage positive negative output current peak collector current single pulse; $t_p \le 1 \text{ ms}$ total power dissipation $T_{amb} \le 25 \text{ °C}$ PEMH15 (SOT363) total power dissipation $T_{amb} \le 25 \text{ °C}$ PEMH15 (SOT363) junction temperature ambient temperature	collector-base voltage open emitter - collector-emitter voltage open base - emitter-base voltage open collector - input voltage positive - negative - output current - peak collector current single pulse; $t_p \le 1 \text{ ms}$ total power dissipation $T_{amb} \le 25 \text{ °C}$ PEMH15 (SOT666) [1][2] - PUMH15 (SOT363) [1] - total power dissipation $T_{amb} \le 25 \text{ °C}$ PEMH15 (SOT666) [1][2] - PUMH15 (SOT363) [1] - interpretation open emitter - collector current sometiment of the position open collector open collect	collector-base voltage open emitter - 50 collector-emitter voltage open base - 50 emitter-base voltage open collector - 10 input voltage positive - +30 negative10 output current - 100 peak collector current single pulse; - 100 total power dissipation $T_{amb} \le 25 ^{\circ}\text{C}$ PEMH15 (SOT363) $T_{amb} \le 25 ^{\circ}\text{C}$ rough total power dissipation $T_{amb} \le 25 ^{\circ}\text{C}$ PEMH15 (SOT363) $T_{amb} \le 25 ^{\circ}\text{C}$ rough total power dissipation $T_$

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

 $[\]begin{tabular}{ll} [2] & Reflow soldering is the only recommended soldering method. \end{tabular}$



6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	ditions Min		Max	Unit
Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMH15 (SOT666)		[1][2]	-	625	K/W
	PUMH15 (SOT363)		<u>[1]</u> -	-	625	K/W
Per device	9					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMH15 (SOT666)		[1][2]	-	417	K/W
	PUMH15 (SOT363)		[1] -	-	417	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

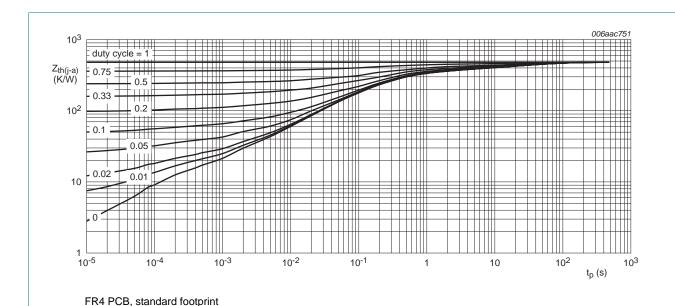


Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMH15 (SOT666); typical values

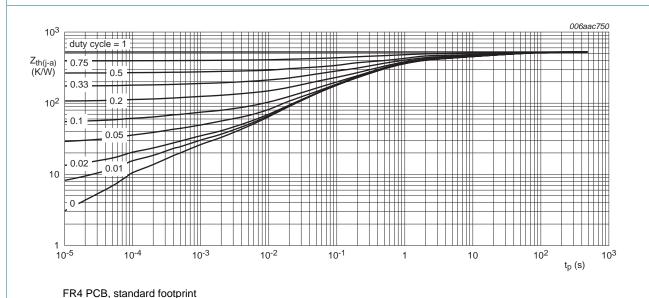


Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMH15 (SOT363); typical values

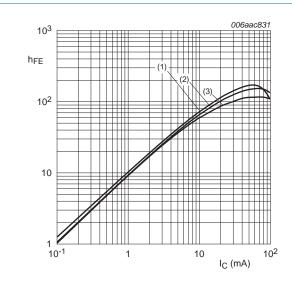
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
Per trans	sistor					
I_{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	900	μА
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	30	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	1.1	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$	2.5	5 1.9	-	V
R1	bias resistor 1 (input)		3.3	3 4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	3 1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	[1] -	230	-	MHz

^[1] Characteristics of built-in transistor



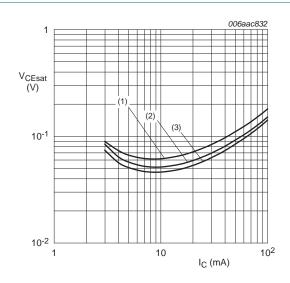
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 4. DC current gain as a function of collector current; typical values



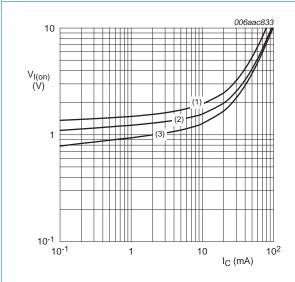
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



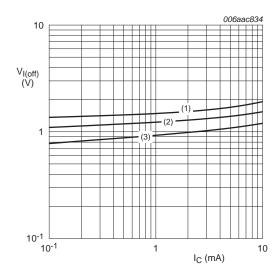
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. On-state input voltage as a function of collector current; typical values



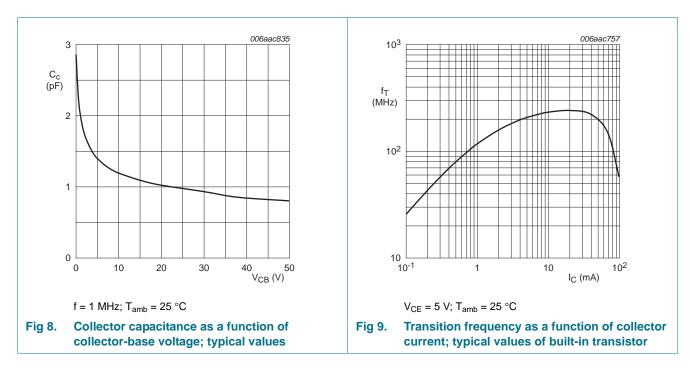
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. Off-state input voltage as a function of collector current; typical values

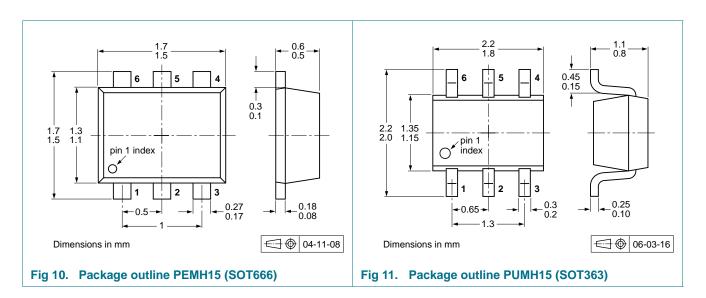


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



PEMH15_PUMH15

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10. Packing information

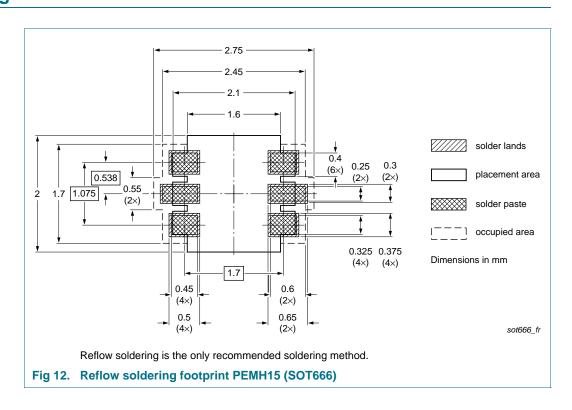
Table 9. Packing methods

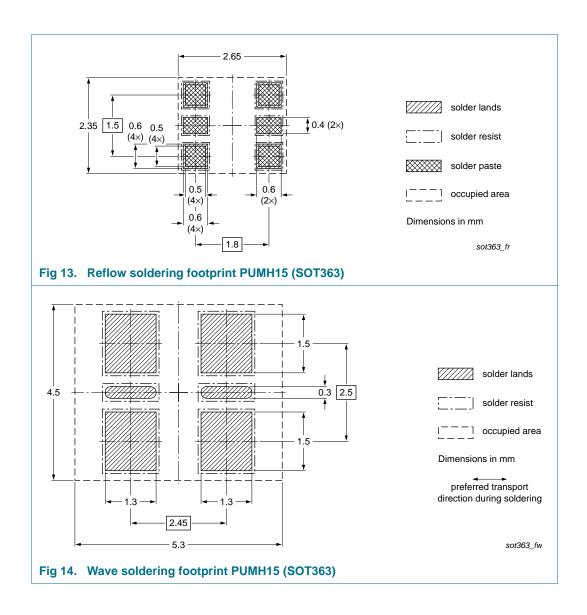
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Туре	Package	Description	Packing quantity				
number				3000	4000	8000	10000
PEMH15	PEMH15 SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMH15	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering





NPN/NPN resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 4.7 kΩ

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH15_PUMH15 v.5	20111216	Product data sheet	-	PEMH15_PUMH15 v.4
Modifications:	 Section 4 "I Figure 1 to Figure 4 to Section 5 "I Section 6 " Table 8 "Ch V_{I(off)} off-sta Section 8 " Section 11 " 	<u>limiting values"</u> : updated Chermal characteristics": up	ed to $V_{I(on)}$ on-state inputed, f_{T} added	it voltage, V _{i(off)} redefined to
PEMH15_PUMH15 v.4	20091115	Product data sheet	-	PEMH15_PUMH15 v.3
PEMH15_PUMH15 v.3	20050211	Product data sheet	-	PUMH15 v.2
PUMH15 v.2	20040414	Product specification	-	PUMH15 v.1
PUMH15 v.1	20031009	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PEMH15_PUMH15

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PEMH15; PUMH15

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

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NSBA144EF3T5G NSVDTA114EET1G 2SC2223-T1B-A 2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G

SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G

DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G